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ITEH58010C6

### 10W,5-6GHz 28V Plastic RF LDMOS Transistor

### **Description**

The ITEH58010C6 is a 10-watt, highly rugged, LDMOS transistor, designed for any general applications at frequencies 5 to 6GHz, in 10\*6mm QFN plastic package, supporting surface mounted on PCB through high density grounding vias.

### It can deliver excellent linearity at 28dBm without DPD.

•Typical 5.7-5.9GHz Class AB RF Performance (On Innogration fixture with device soldered).

 $V_{dS}$ = 28V,  $I_{dq}$ =100mA,  $V_{gs}$  =2.74V

Eroa	Pulse CW Signal <sup>(1)</sup>			P <sub>avg</sub> =3	2dBm WCDM	A Signal <sup>(2)</sup>
Freq (GHz)	Gain P1 (dB)	P3dB (W)	Eff (%)	Gp (dB)	η₀ (%)	ACPR <sub>5M</sub> (dBc)
5.7	11.6	11.6	38	12.5	17.5	-41.2
5.8	11.5	11.8	40	12.6	18.1	-39.4
5.9	11.5	11.9	39	12.1	17.8	-40.8

### **Features**

- High Efficiency and Linear Gain Operations
- Integrated ESD Protection
- · Excellent thermal stability, low HCI drift

### Suitable Applications

- C band power amplifier
- 5G cellular power amplifier within 5-6GHz
- · WIFI High power access point
- GaAs HBT lower cost replacement

- Large Positive and Negative Gate/Source Voltage Range for Improved Class C Operation
- Pb-free, RoHS-compliant

**Table 1. Maximum Ratings** 

Rating	Symbol	Value	Unit	
DrainSource Voltage	V <sub>DSS</sub>	+65	Vdc	
GateSource Voltage	V <sub>GS</sub>	-10 to +10	Vdc	
Operating Voltage	V <sub>DD</sub>	+28	Vdc	
Storage Temperature Range	Tstg	-65 to +150	°C	
Case Operating Temperature	T <sub>c</sub>	+150	°C	
Operating Junction Temperature	T <sub>J</sub>	+225	°C	

#### **Table 2. Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	Do 10	4.0	°C/W
T <sub>C</sub> = 85°C, T <sub>J</sub> =200°C, DC test	R⊕JC	1.8	-0/٧٧

### **Table 3. ESD Protection Characteristics**

Test Methodology	Class	
Human Body Model (per JESD22A114)	Class 2	

Table 4. Electrical Characteristics (TA = 25 °C unless otherwise noted)



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Characteristic		Min	Тур	Max	Unit
DC Characteristics					
Drain-Source Voltage	V		65		V
V <sub>GS</sub> =0, I <sub>DS</sub> =100uA	V <sub>(BR)DSS</sub>		00		V
Zero Gate Voltage Drain Leakage Current				1	^
$(V_{DS} = 28V, V_{GS} = 0 V)$	IDSS			ı	μΑ
GateSource Leakage Current				1	^
$(V_{GS} = 11 \text{ V}, V_{DS} = 0 \text{ V})$	I <sub>GSS</sub>			ı	μΑ
Gate Threshold Voltage	\/ (45)		2		V
$(V_{DS} = 28V, I_D = 600 \mu A)$	V <sub>GS</sub> (th)		2		V
Gate Quiescent Voltage	V		2.7		V
$(V_{DD}$ = 28V, $I_D$ = 100mA, Measured in Functional Test)	$V_{GS(Q)}$		2.7		V

 $\textbf{Load Mismatch (In Innogration Test Fixture, 50 ohm system):} \quad V_{DD} = 28 V dc, \ I_{DQ} = 100 mA, \ f = 6000 \ MHz$ 

VSWR 10:1 at 10W pulse CW Output Power No Device Degradation

Figure 1:Pin Definition(Top View)



Pin No.	Symbol	Description
8,9,10,11,14,15,16,17	Vgs/RF In	Vgs and RF input
26,27,28,29,32,33,34,35	Vds/RF out	Vds and RF output
2,5,7,12,13,18,20,23,25,30,31,36	GND	DC/RF Ground
Others	NC	No connection
Package Base	GND	DC/RF Ground.



# Reference Circuit of Test Fixture Assembly Diagram 5700-5900MHz RO4350B 20mils

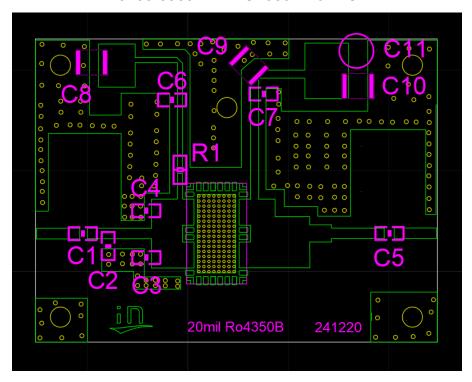


Figure 2. Test Circuit Component Layout

**Table 5. Test Circuit Component Designations and Values** 

Component	Value	Quantity
U1	ITEH58010C6	1
C1、 C5、C6、C7	3.9pF	4
C2、 C3、C4	0.3pF	3
C8、C9、C10	10uF/63V	3
C11	470uF/63V	1
R1	10 Ω	1



### TYPICAL CHARACTERISTICS

Figure 3. Power Gain and Drain Efficiency as function of Power Out

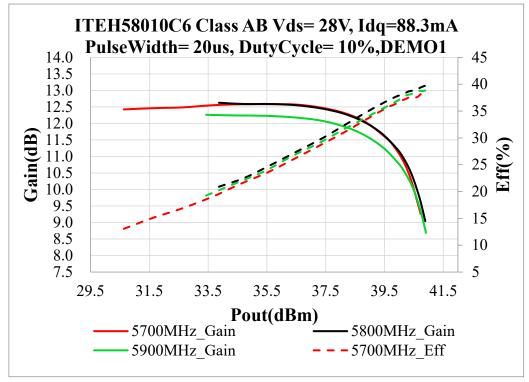


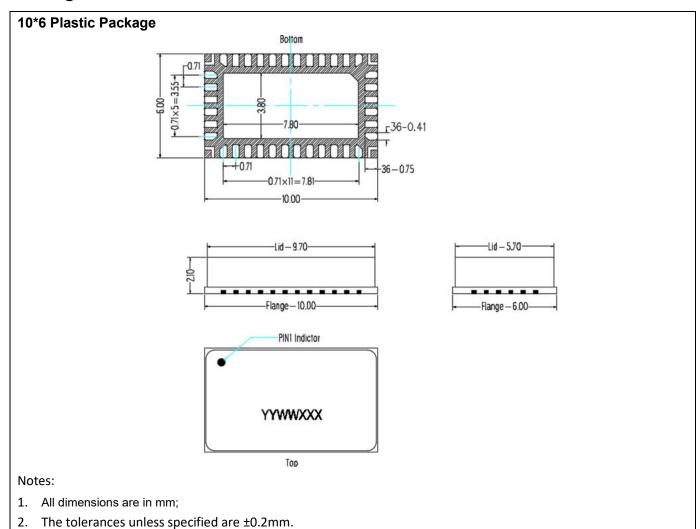
Figure 4.Network analyzer output S11/S21





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### **Package Dimensions**



### Revision history

Table 7. Document revision history

Date	Revision	Datasheet Status
2025/8/6	Rev 1.0	Preliminary Datasheet

### Application data based on ZYX-25-33

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